IN THE CLAIMS:

Serial No.: 09/892,130

1. (Allowed) A method of rinsing a wafer comprising: spinning a wafer;

exposing said spinning wafer to DI water while providing sonic waves to substantially the entire surface area of the wafer; and

after exposing said spinning wafer to DI water, exposing said spinning wafer to a liquid or vapor having a lower surface tension than water.

- 2. (Allowed) The method of claim 1 wherein said liquid is or vapor comprises isopropyl alcohol (IPA).
- 3. (Allowed) The method of claim 1 wherein said sonic waves are applied to the backside of said wafer.
- 4. (Allowed) The method of claim 1 further comprising the step of heating said DI water to a temperature greater than room temperature prior to exposing said spinning wafer to said DI water.
- 5. (Allowed) The method of claim 1 wherein said wafer is spun at a rate between 50-1000 rpms while exposing said wafer to said DI water and to said liquid or vapor.

-2-

AMAT Ref: 4733 USA/W-C/W-C/JB1 BSTZ Ref: 4887.P446

- 6. (Currently Amended) The method of claim 2 wherein the time of exposure to said liquid <u>or vapor</u> is less than <u>the</u> time of exposure to said DI water or vapor.
 - 34. (Allowed) A method of rinsing a wafer comprising: spinning a wafer;

exposing said spinning wafer to water while providing sonic waves to substantially the entire surface area of the wafer; and

after exposing said spinning wafer to water, exposing said spinning wafer to a liquid or vapor having a lower surface tension than water.

- 35. (Allowed) The method of claim 34 wherein said liquid or vapor comprises isopropyl alcohol (IPA).
- 36. (Allowed) The method of claim 34 wherein said sonic waves are applied to the backside of said wafer.
- 37. (Currently Amended) The method of claim 34 further comprising the step of heating said DI water to a temperature greater than room temperature prior to exposing said spinning wafer to said water.
- 38. (Allowed) The method of claim 34 wherein said wafer is spun at a rate between 50-1000 rpms while exposing said wafer to said water and to said liquid or vapor.

- 3 -

Serial No.: 09/892,130

AMAT Ref: 4733 USA/W-C/W-C/JB1 BSTZ Ref: 4887.P446 39. (Currently Amended) The method of claim 35 wherein the time of exposure to said liquid <u>or vapor</u> is less <u>the</u> than time of exposure to said water or vapor.

Serial No.: 09/892,130

Invitation for a telephone interview

The Examiner is requested to call the undersigned at (408) 720-8300 if there remains any issue with allowance of this case.

Charge our Deposit Account

Please charge any shortage to our Deposit Account No. 02-2666.

Respectfully submitted,

BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN

Date: 1/20/05

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Serial No.: 09/892,130

- 5 -

AMAT Ref: 4733 USA/W-C/W-C/JB1 BSTZ Ref: 4887.P446